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Time resolution of an irradiated 3D silicon pixel detector

We report on the measurements of time resolution for double-sided 3D pixel sensors with a single cell of $50\ \mu\text{m} \times 50\ \mu\text{m}$ and thickness of $285\ \mu\text{m}$, fabricated at IMB-CNM and irradiated with reactor neutrons to different radiation doses up to $1e16\ \text{MeV neq/cm}^2$.

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